



MEMs Technology in Testing

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Working for your future!



Overview:

- 1. Where are we ?*
- 2. Core Technology*
- 3. **accipiter**[®] Structure*
- 4. In the real world*
- 5. What's next?*



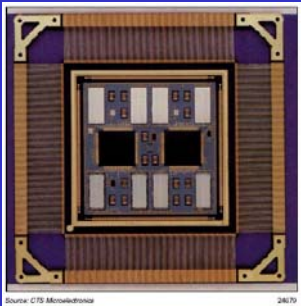
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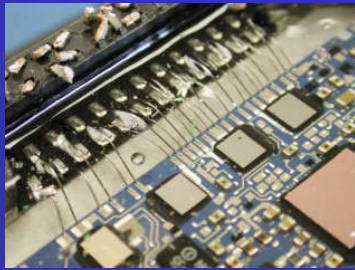
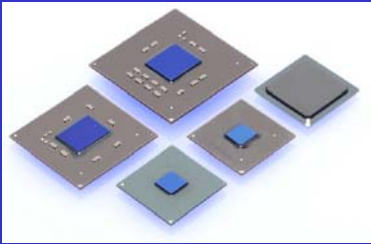
Where are we?!

Technical Trend

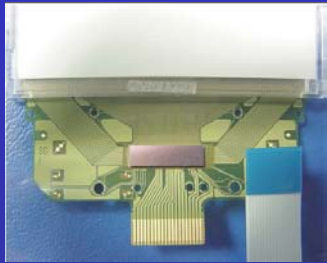
- **Package**
 - Lighter / Thinner/ Shorter/ Smaller
- **Performance**
 - Higher Speed/ Lower power
- **Process**
 - Smaller Geometry / Smaller reliability margin



Flip Chip
MCM
Direct Die Attach (COB)



Final test on Wafer Level



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Core Technology:

Micro Tip Process

MEMs & Integration....

- Advanced die testing
 - Better Reliability
- Economical Manufacturing

Ceramic Technology

Ultra LTCC ...

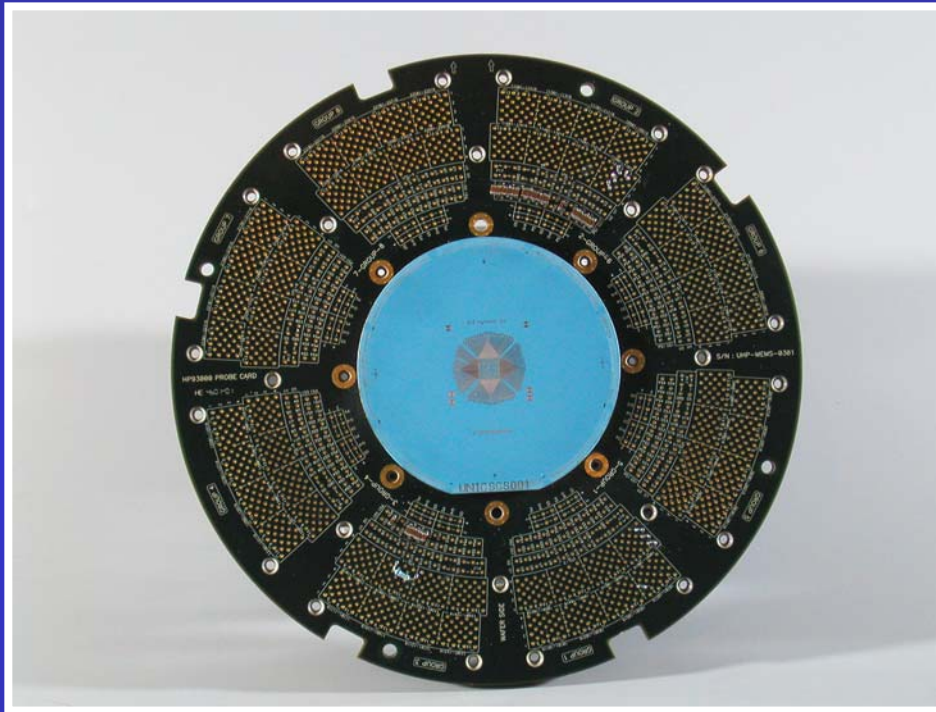
- Multiple Layers
 - High Vias
 - Large Areas
- Extreme Flatness
 - CTE Factor
 - Bandwidth

**Low Temperature Co-fire Ceramic is co-fired at 900 C*

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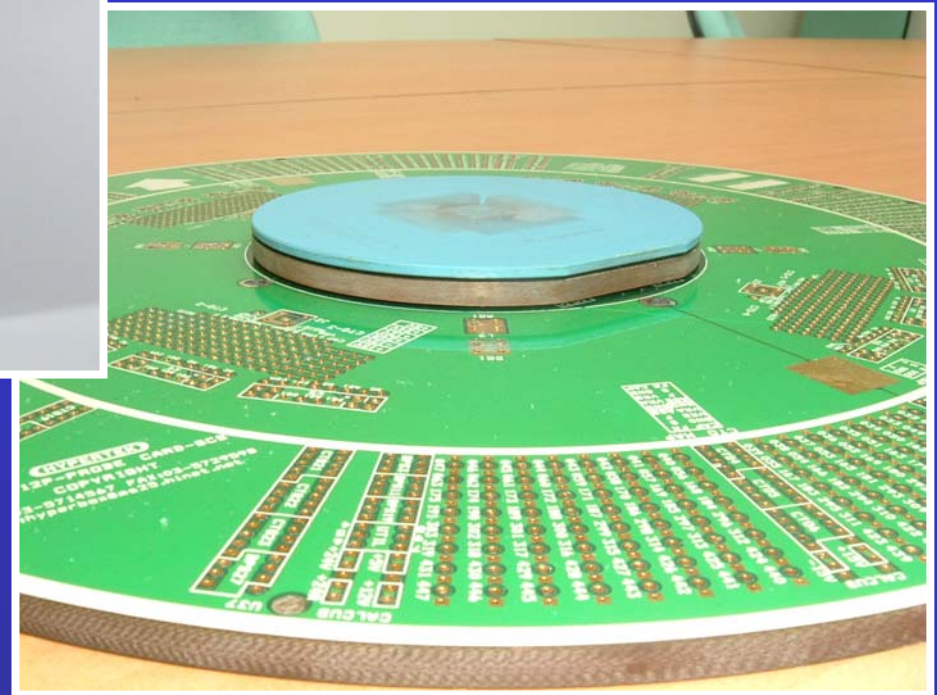


1. accipiter[®] Structure:



**for Agilent 93000 , probe depth 120 mil*

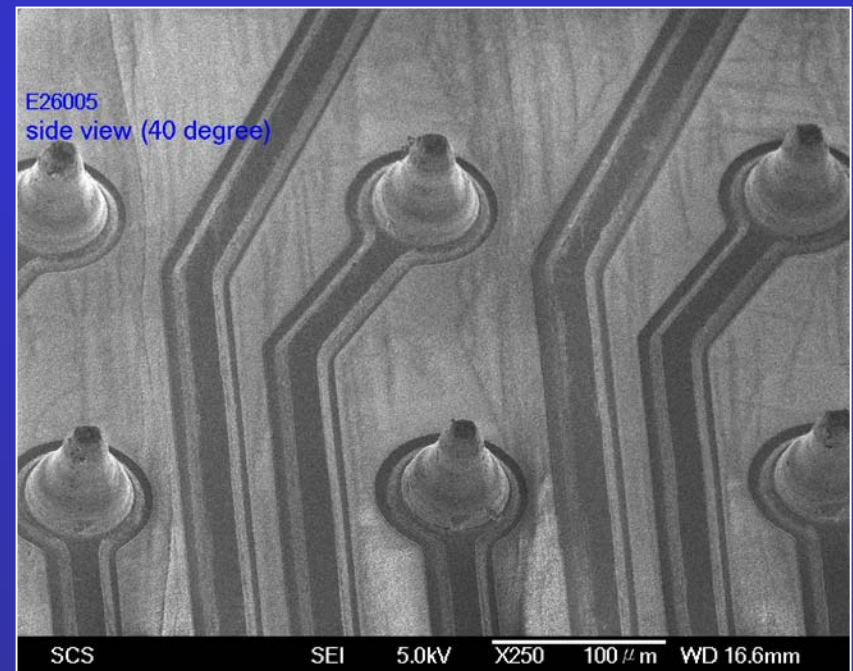
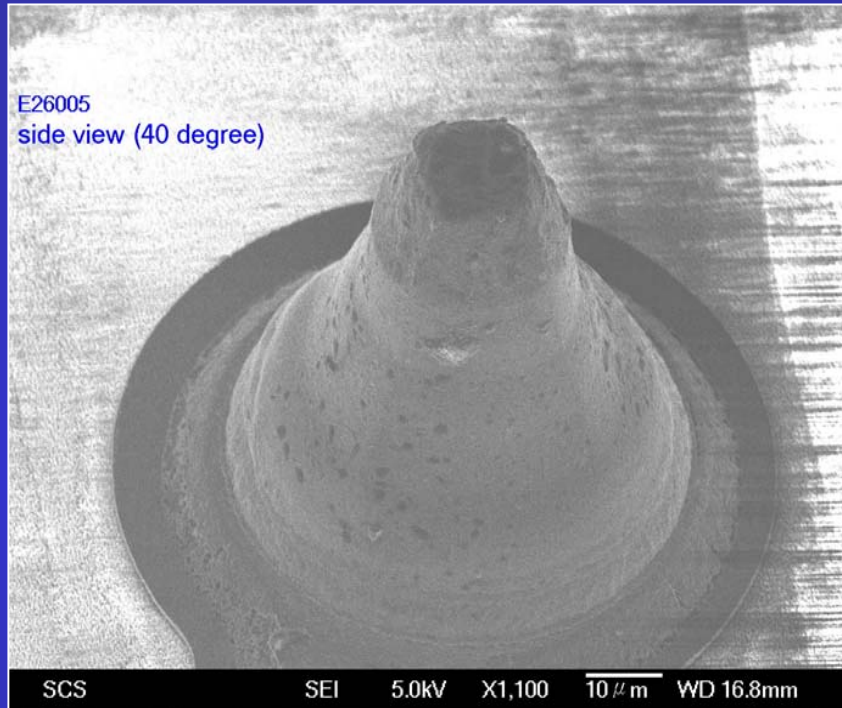
**for Credence/Quartet , probe depth 320 mil*



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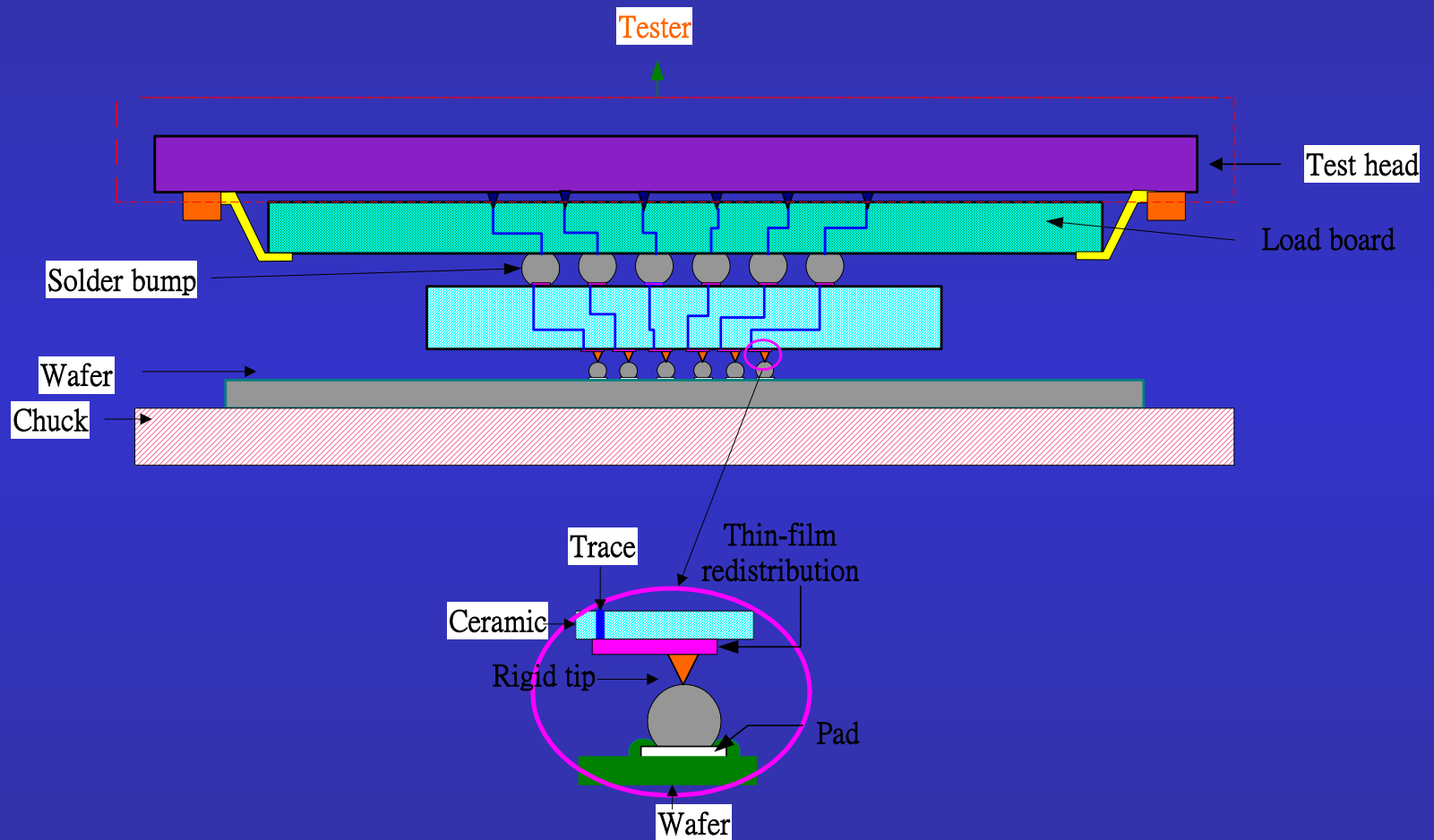
1. accipiter® Structure:



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1. accipiter[®] Structure:





Benefit of MEMs + ULTCC:

- Up to 2048 I/O design.
- Non- pin count relative cost structure.
- High Speed Device Probing-3GHz bandwidth
 - Low impedance -- shorter trace length
 - High noise inhabitant -- dielectric constant :
7.8
- High accuracy - same level with fab process
- Low contact damage- tip dimension 7 ~ 12 μm
- High Planarity- within 3 μm
- Less than 2 weeks for repeat order.
- Long life time. Estimate 1M insertions.

Electrical Characteristic – Impedance (1)

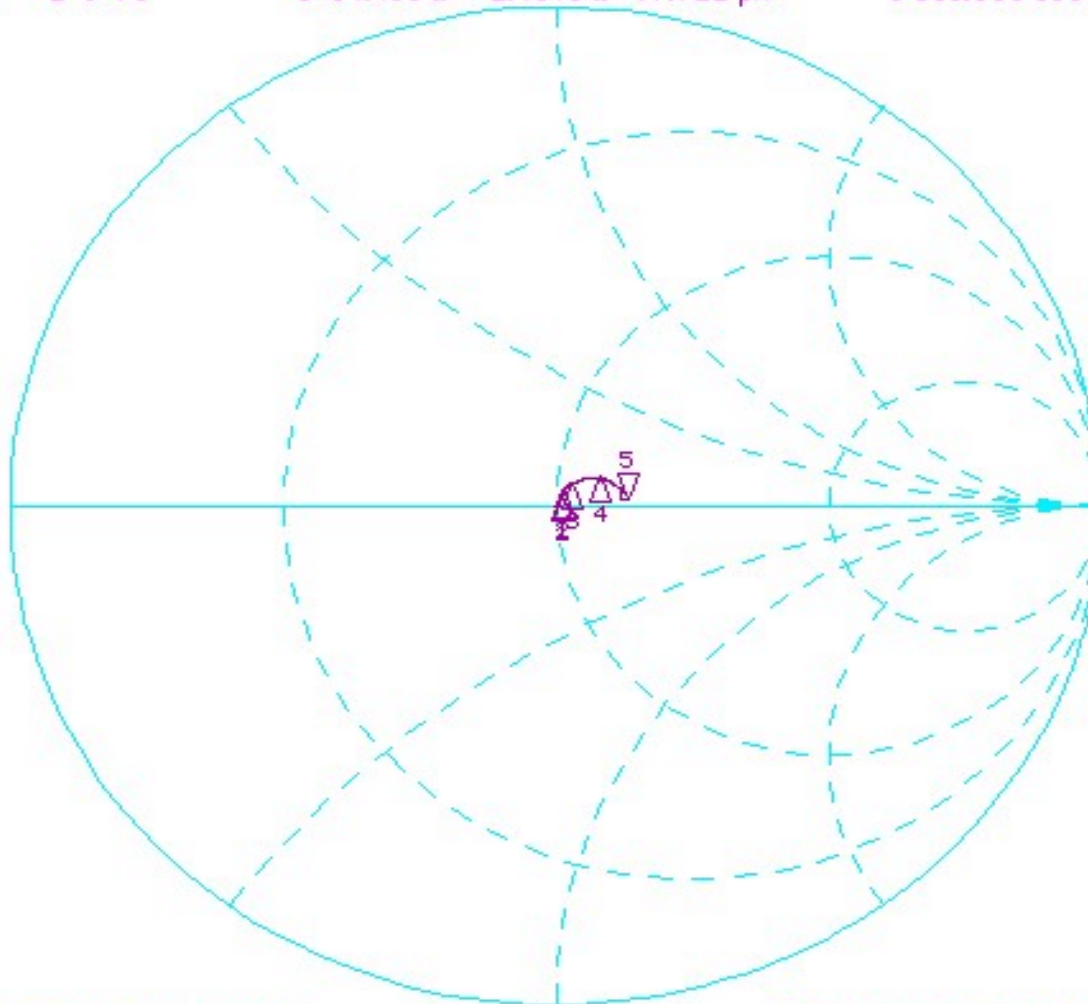
29 Apr 2002 14:38:55

CH1 S11 1 U FS 5: 64.430 Ω 1.4648 Ω 77.712 μH 3 000.000 000 MHz

*

Cor

↑



CH1 Markers

1: 50.635 Ω
1.5508 Ω
300.000 MHz

2: 50.977 Ω
2.4238 Ω
500.000 MHz

3: 52.539 Ω
4.5234 Ω
1.00000 GHz

4: 58.166 Ω
6.5391 Ω
2.00000 GHz

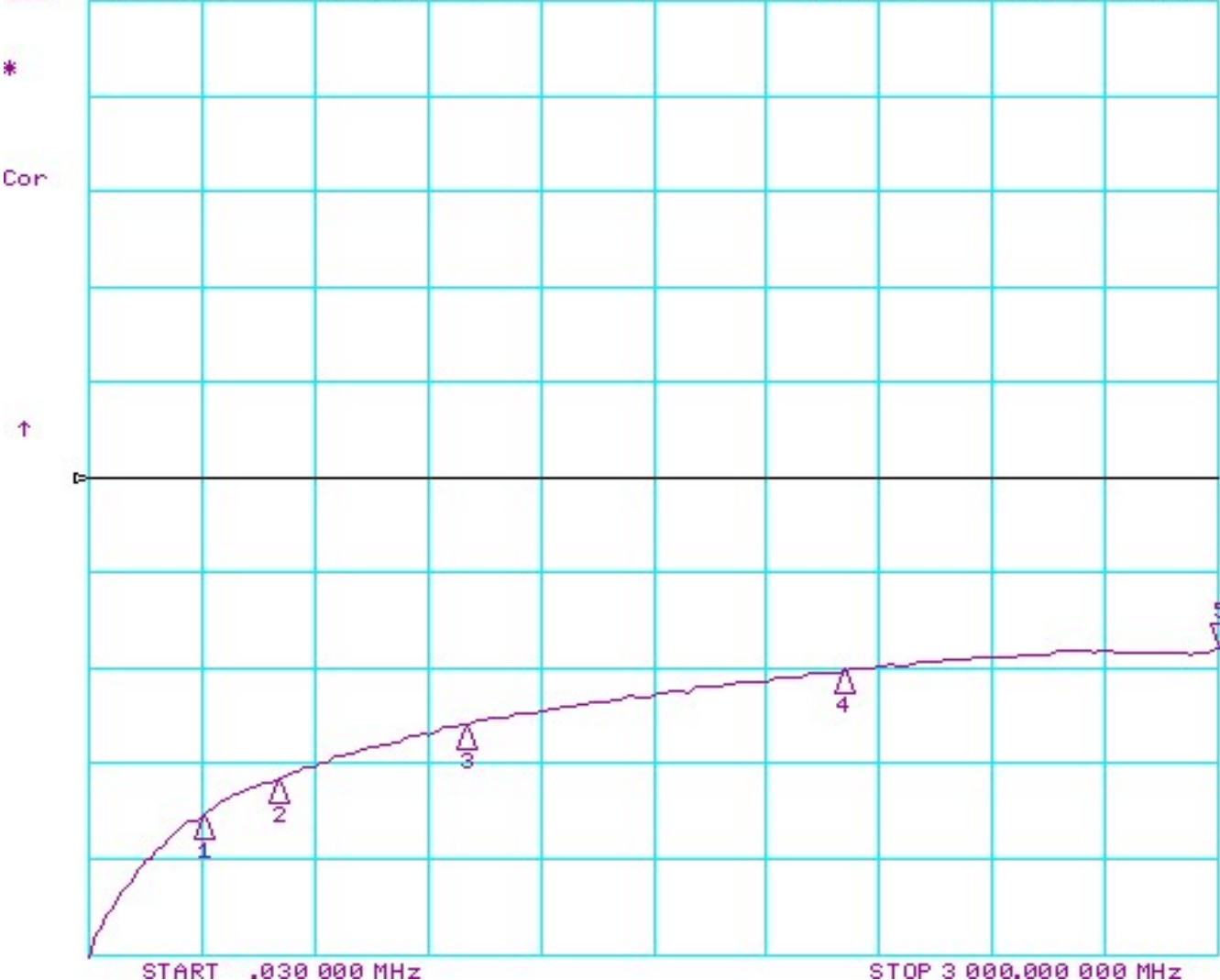
START .030 000 MHz

STOP 3 000.000 000 MHz

Electrical Characteristic – Return loss (2)

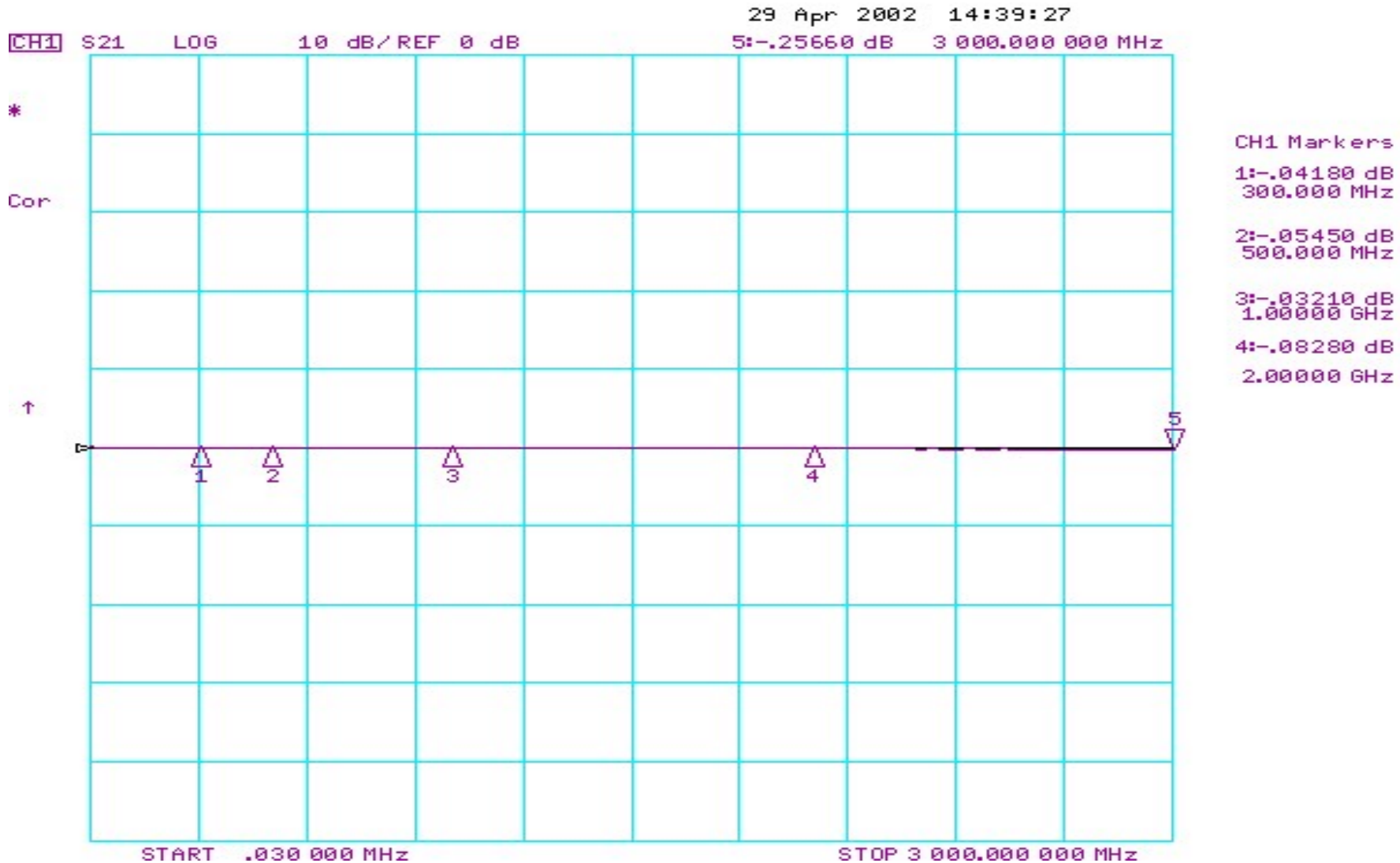
29 Apr 2002 14:39:12

CH1 S11 LOG 10 dB/REF 0 dB 5:-17.881 dB 3 000.000 000 MHz



CH1 Markers
1:-35.614 dB
300.000 MHz
2:-31.735 dB
500.000 MHz
3:-26.022 dB
1.00000 GHz
4:-20.311 dB
2.00000 GHz

Electrical Characteristic – Insertion loss (3)





Specification:

<i>Tip Dimesions</i>	7~12 um
<i>Probe Tip Height</i>	75 um
<i>Max. Probing area</i>	4"
<i>Min. Probing Pitch</i>	90um/Array
<i>Accuracy</i>	+/- 1um
<i>Planality</i>	< 3 um
<i>Max. Current</i>	800 mA
<i>Shear Force</i>	100 g / pin
<i>Major Material</i>	Ni/Tip, Cu/trace
<i>Path RES.</i>	< 2 Ohm
<i>Impedance Match</i>	50 Ohm +/- 10%
<i>Leakage</i>	< 10nA @ 5V
<i>1st Order L/T</i>	5 weeks
<i>Repeat Order L/T</i>	< 2 weeks



Life time analysis

Subject: SCS MEMS VPC for 8" wafers(633 pins)
Tester/Prober: Agilent 93000/P600, P12/TEL
Clean sheet: Enhanced 3M type C(*type C + polish paper/pink type*)
Tool: Olympus microscope with micro meter
Reading: Check pin high twice(from ULTCC to tip) for average.

Result:

- 1. The wear out rate is around 3~6um after 6000 times clean.*
- 2. In the bumping probing simulation experiment, there is almost no wear out (pin height) after 250K insertions*



Before



After 15K times



After 120K times



After 250K times

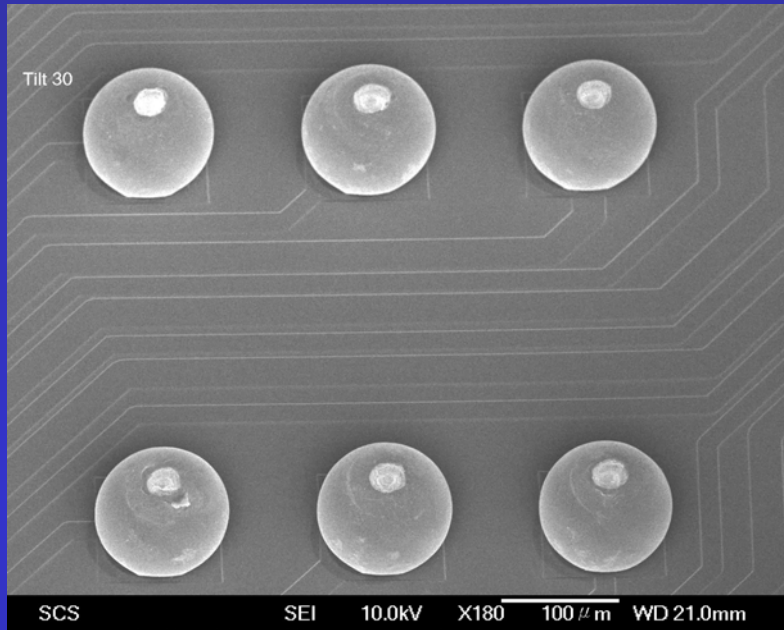


In the real world: ***production running***

- ***Device:*** Graphic Chip, 300mm wafers(1699 pins)
- ***Facility:*** Agilent 93000/P600 with TEL/P12
- ***Production units:*** 15 lots(around 100K insertions)
- ***Probing result:***
 - Yield is around 2 % better than conventional VPC.
 - 1st yield is almost equal to final yield.
 - Limited maintenance needed,brush cleaning only during the production.



In the real world:



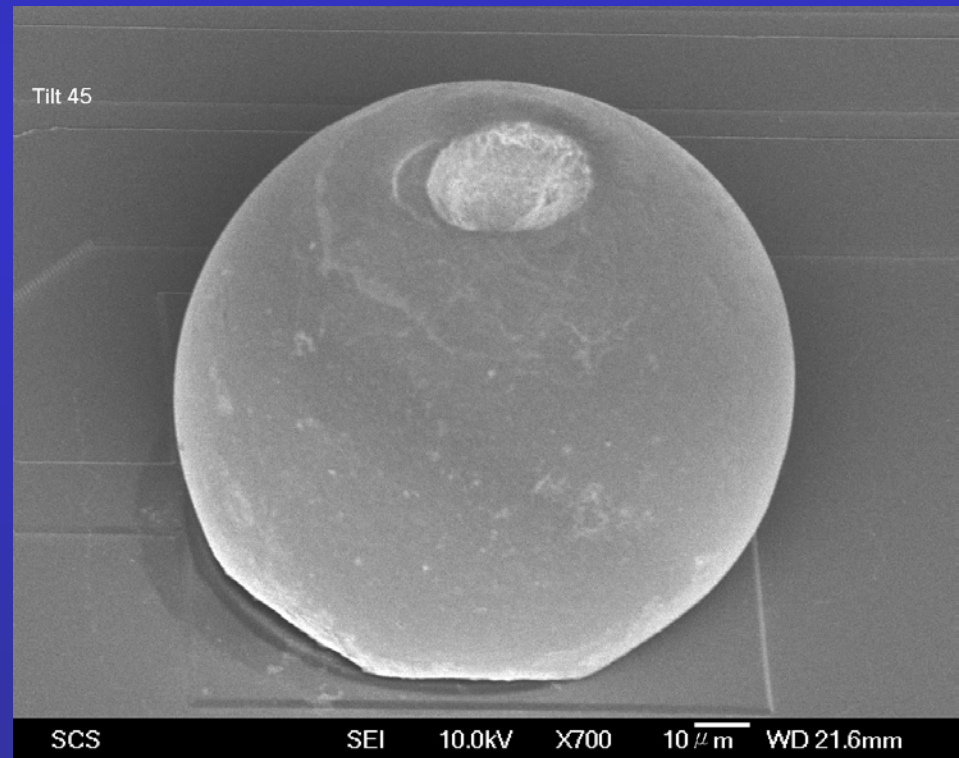
Probing set-up:

O/D: 90um

Dimple dimension: 30 um

Dimple depth: 20 um

Dimple size is around 1.2~1.6% of bump size.



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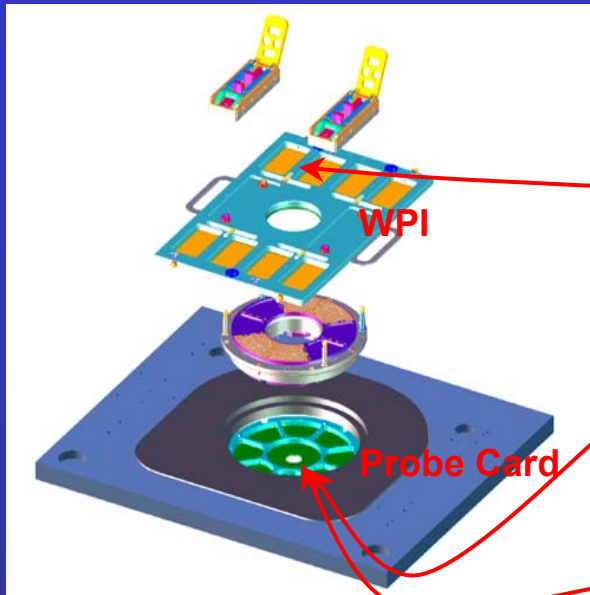


What's Next?

➤ Speed sort in CP stage?

One of our customer set-up a project to simulate the possibility of speed testing in wafer sort stage, he simulate a signal in different frequency and measure this signal in different point of the test environment.

Tester: Agilent 93000/P600 and Network analyzer



Step 1

check at Pogo Pin

Step 2

Check/probe at Wired Type vertical probe card (on the solder point)

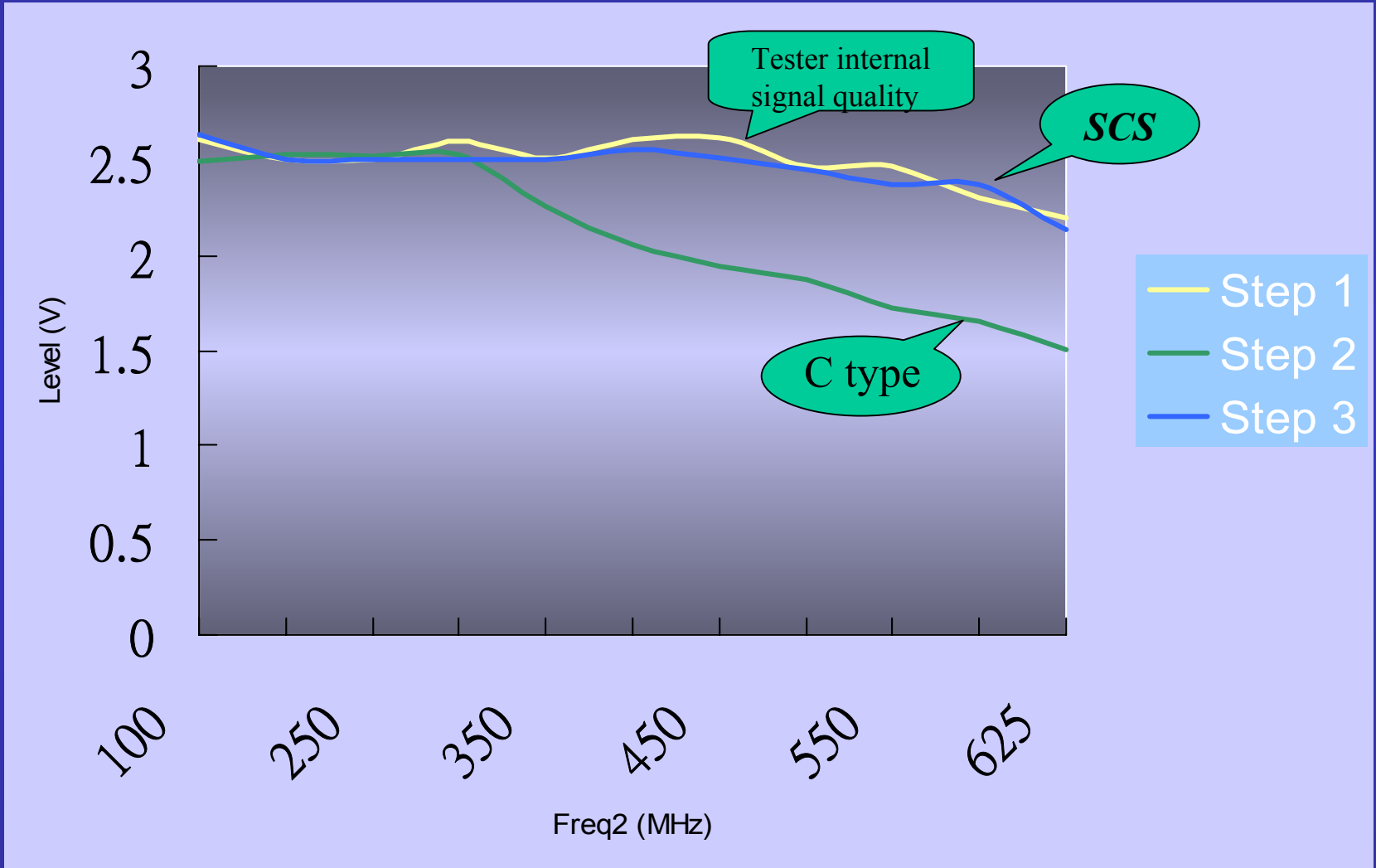
Step 3

Check/probe at SCS Probe Card

5 → with SCS accipiter (on the top of needle)



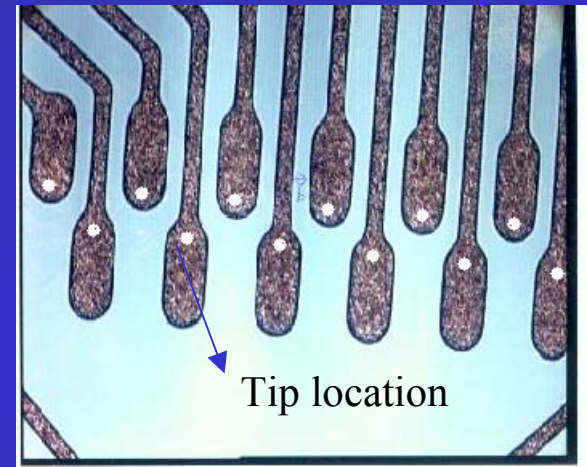
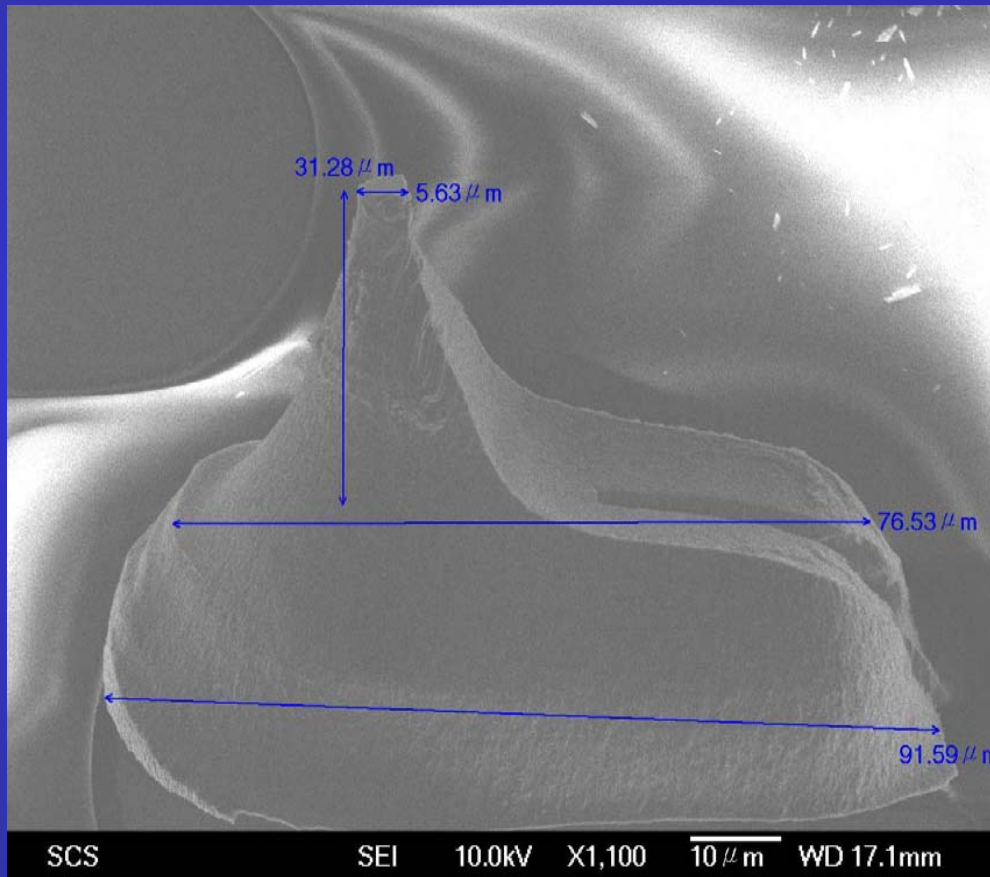
➤ Speed sort in CP stage?





What's Next?

➤ 45um/linear bump pitch probing?



Object: LCD driver
Bump: Au bump
Bump size: 17Hx32Wx65L
Bump pitch: 40um

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Conclusion:

- Rigid tip design for VPC is a good design for wafer testing.
- Rigid tip design perform low maintenance needed and reduce the risk of probe card damage.
- As tester price getting higher and higher, utilization rate of VPC is a essential mark of profit.
- MEMs + LTCC technology should be able to apply in bare die B/I test for memory device.